
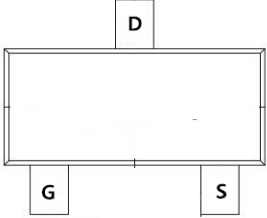
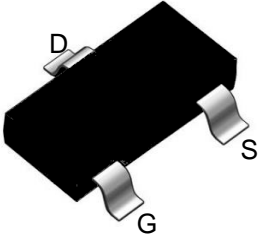
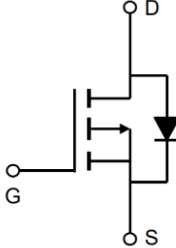


TM06P03MI

P-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = -30V$ $I_D = -6.2A$ $R_{DS(ON)} = 25m\Omega(Typ.) @ V_{GS} = -10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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MI:SOT-23-3L

Marking: 30P06

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Max.	Units	
V_{DSS}	Drain-Source Voltage	-30	V	
V_{GSS}	Gate-Source Voltage	± 20	V	
I_D	Continuous Drain Current	$T_A = 25^\circ C$	-6.2	A
		$T_A = 100^\circ C$	-4.6	A
I_{DM}	Pulsed Drain Current <small>note1</small>	-30	A	
P_D	Power Dissipation $T_A = 25^\circ C$	1.5	W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	61.7	$^\circ C/W$	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$	

TM06P03MI
P-Channel Enhancement Mosfet
Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V,$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=-10V, I_D=-7A$	-	25	28	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	-	29	39	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	782	-	pF
C_{oss}	Output Capacitance		-	135	-	pF
C_{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q_g	Total Gate Charge	$V_{DS}=-15V, I_D=-4A,$ $V_{GS}=-10V$	-	10	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-15V, I_D=-7A,$ $V_{GS}=-10V, R_{GEN}=2.5\Omega$	-	11	-	ns
t_r	Turn-on Rise Time		-	19	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	45	-	ns
t_f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-6.2	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-28	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-7A$	-	-0.8	-1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

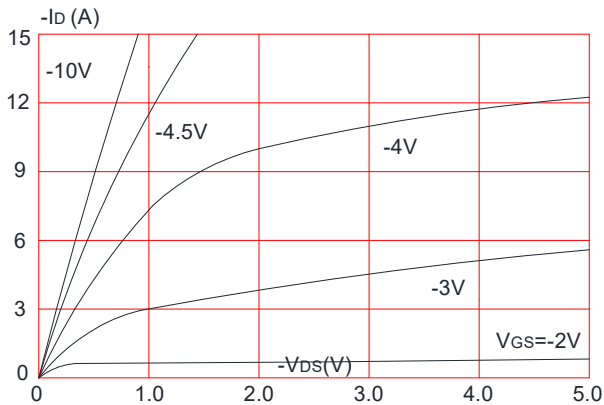


Figure 2: Typical Transfer Characteristics

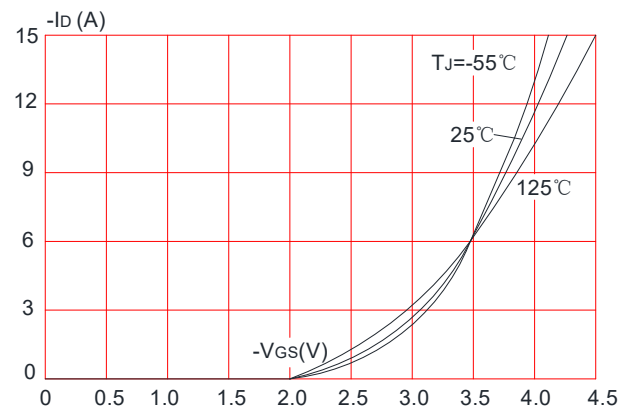


Figure 3: On-resistance vs. Drain Current

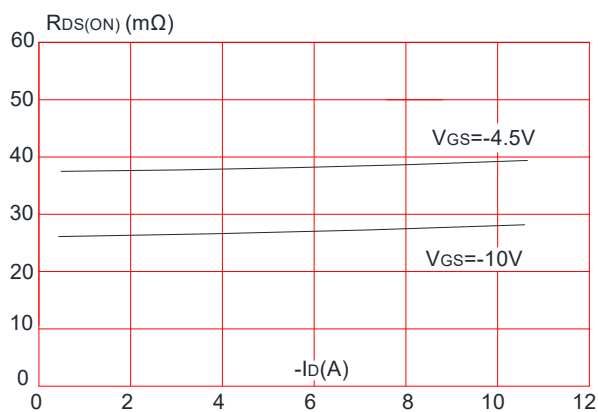


Figure 4: Body Diode Characteristics

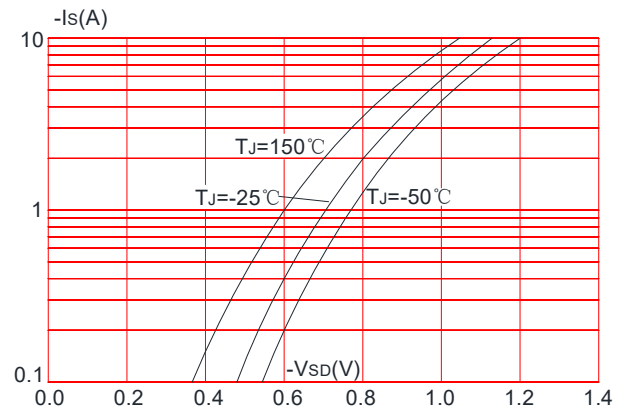


Figure 5: Gate Charge Characteristics

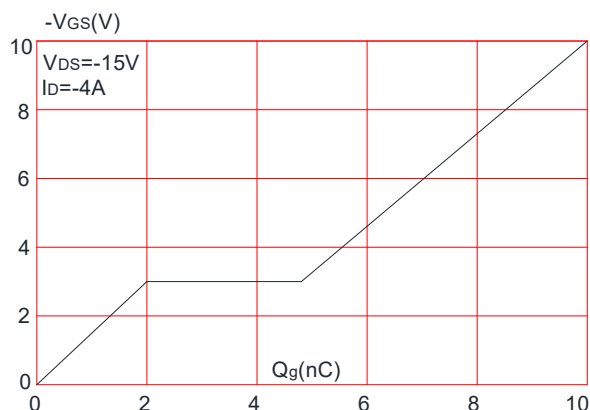
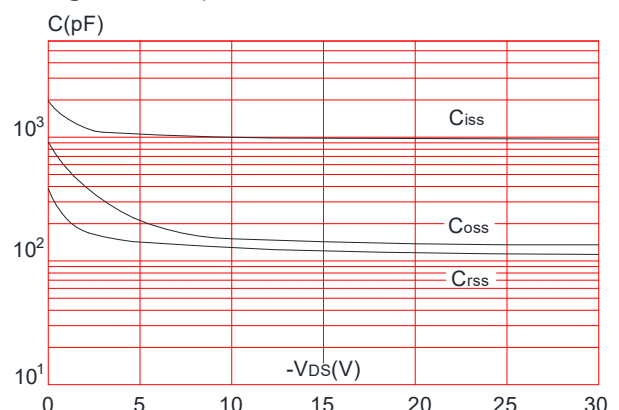


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

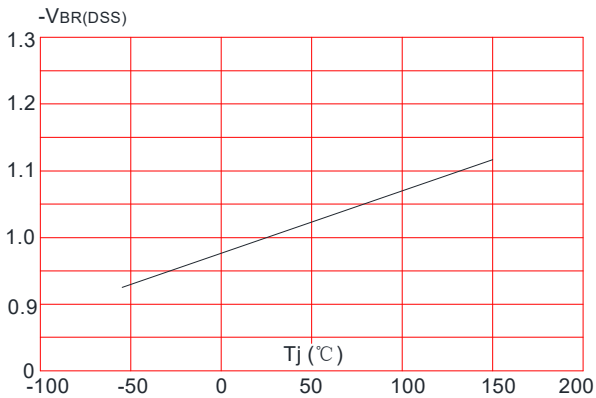


Figure 8: Normalized on Resistance vs. Junction Temperature

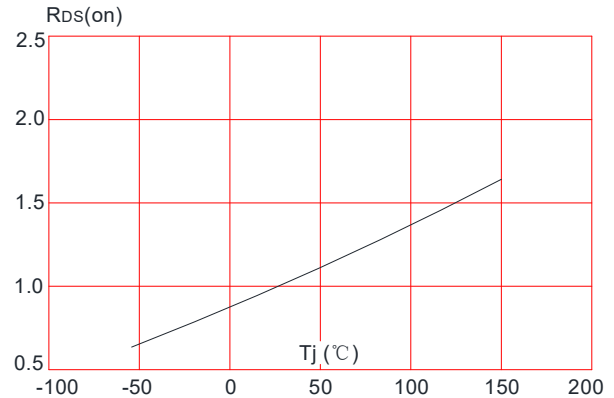


Figure 9: Maximum Safe Operating Area

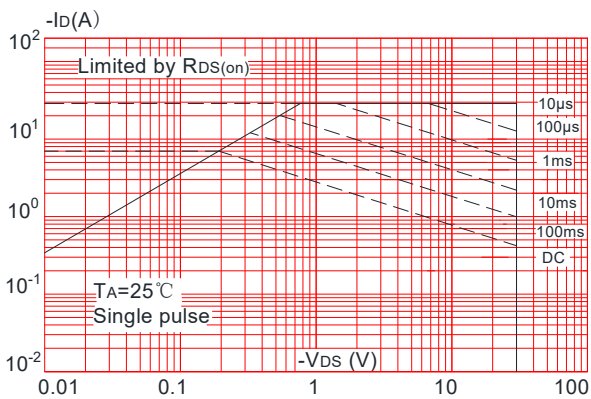
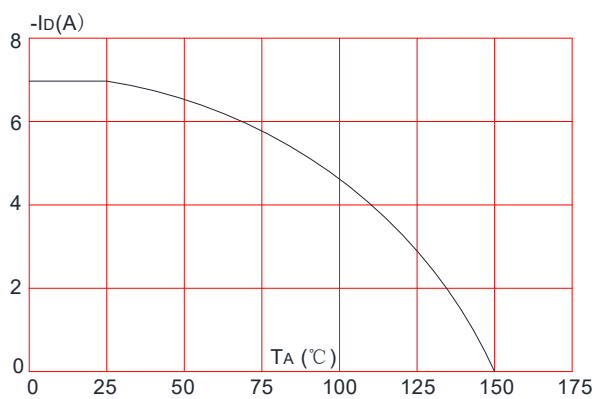
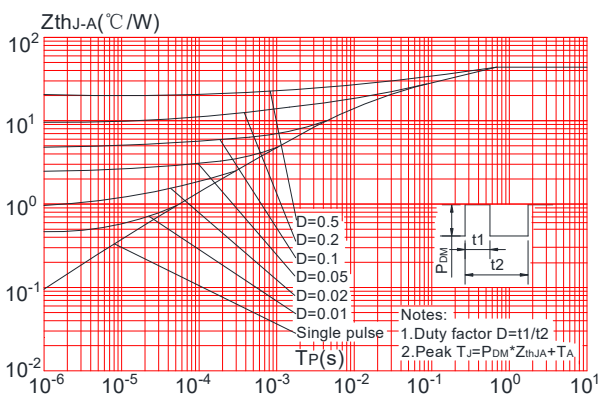


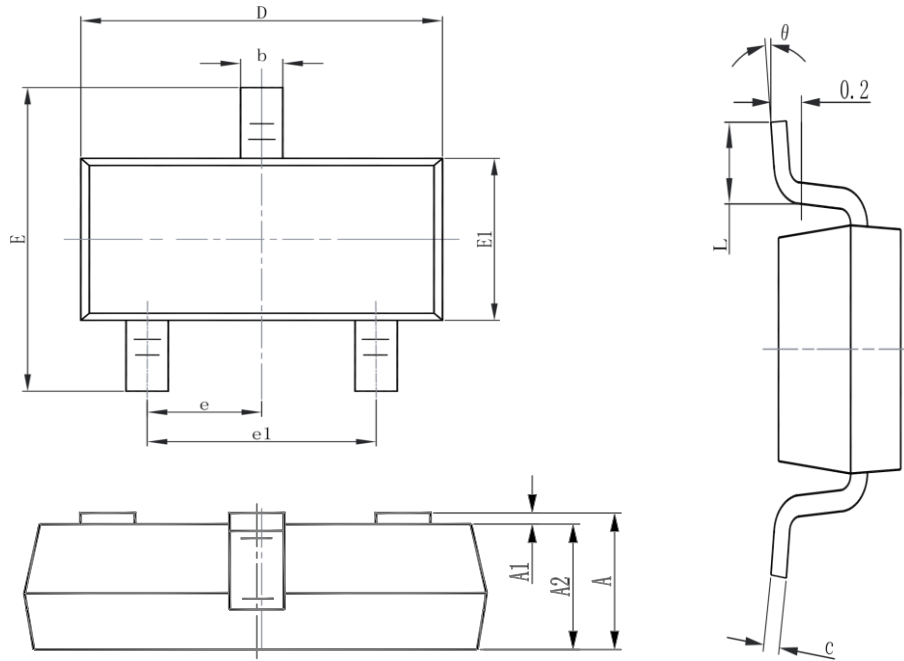
Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature



Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°